

EAST - [back.wsp:1]

File View Edit Tools Window Help

Drafts  
BRS:  
Pending  
Active  
L2: (1) ("59782850" OR "6028782").PN.  
L3: (1722658) reference  
L4: (255685) cell  
L5: (2040) (3 ADJ 4)  
L6: (207844) cells  
L7: (858) (3 ADJ 6)  
L8: (2301) (7 OR 5)  
L10: (1) (2 AND 8)  
L11: (2) ("5978250" OR "6028782").PN.  
L13: (2) (11 AND 8)  
L14: (555) 365/145.ccls.  
L16: (16167) dummy  
L17: (303180) (6 OR 4)  
L18: (1197) (16 ADJ 17)  
L19: (3400) (18 OR 8)  
L21: (110) (14 AND 19)  
Failed  
Saved  
Favorites  
UDC  
Queue  
Trash

Search  
DB: USPAT  
Default operator: OR  
(14 AND 19)

BRS form IS&R form Image Text

	U	I	Document ID	Issue Date	Pages	Title	Current OR Δ	Current XRef Δ
1	<input type="checkbox"/>	<input type="checkbox"/>	US 5969380 A	19991019	15	Three dimensional ferroelectric	257/295	365/145
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5652445 A	19970729	29	Hybrid hall effect device and	257/295	257/421
3	<input type="checkbox"/>	<input type="checkbox"/>	US 5565695 A	19961015	20	Magnetic spin transistor hybrid	257/295	257/421

Ready NUM

EAST - [back.wsp:1]

File View Edit Tools Window Help

Drafts  
Pending  
Active  
L1: (0) kang-young-min.in.  
L2: (2587883) "3"  
L3: (2110903) "8"  
L4: (846701) (3 SAME 2)  
L5: (35385) nand  
L6: (7105) ferroelectric  
L7: (1722658) reference  
L8: (255685) cell  
L9: (16167) dummy  
L10: (287726) column  
L11: (987) (9 ADJ 8)  
L12: (2040) (7 ADJ 8)  
L13: (2961) (11 OR 12)  
L15: (31) (14 SAME 10)  
L16: (2755) (5 SAME 4)  
L17: (0) 14 and 16  
L19: (10) (15 AND 5)  
L20: (105) (13 SAME 6)  
Failed  
Saved  
Favorites  
UDC  
Online

SEARCH [ ] [ ] [ ] [ ] [ ]  
DBs: USPAT [ ] Plurals [ ] Synonyms [ ]  
Default operator: OR [ ]  
(13 SAME 6) [ ]  
BRS form [ ] IS&R form [ ] Image [ ] Text [ ]

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6034387 A	20000307	9	Methods of operating ferroelectric	257/295	257/296
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5969380 A	19991019	15	Three dimensional ferroelectric	257/295	365/145
3	<input type="checkbox"/>	<input type="checkbox"/>	US 5932903 A	19990803	32	Ferroelectric semiconductor memory	257/295	365/145

Ready NUM





